

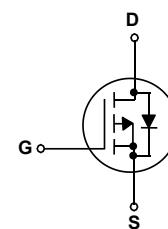
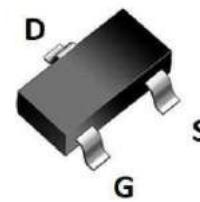


Features

- P-Channel
- Fast switching
- Very Low On-resistance $R_{DS(ON)}$
- Low Crss
- Improved dv/dt capability

V_{DS}	-20	V
$R_{DS(on),TYP} @ V_{GS}=-4.5\text{ V}$	42	mΩ
$R_{DS(on),TYP} @ V_{GS}=-2.5\text{ V}$	65	mΩ
I_D	-3	A

SOT-23



Part ID	Package Type	Marking	Packing
ZT2301A	SOT-23	2301	3000pcs/Reel

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	± 10	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-20	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-55 to 150	°C	
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C	
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c=25^\circ\text{C}$	-12	A
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous	$T_c=25^\circ\text{C}$	-3	A
		$T_c=100^\circ\text{C}$	-1.9	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	1.1	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	105	°C/W	



Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ $T_J=25^\circ\text{C}$ (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-20	--	--	V
Idss	Zero Gate Voltage Drain Current	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$	--	--	-1	μA
IGSS	Gate-Body Leakage Current	$V_{GS}=\pm 10\text{V}, V_{DS}=0\text{V}$	--	--	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.4	-0.7	-1.1	V
RDS(on)	Drain-Source On-State Resistance	$V_{GS}=-4.5\text{V}, I_D=-3\text{A}$	--	42	70	$\text{m}\Omega$
RDS(on)	Drain-Source On-State Resistance	$V_{GS}=-2.5\text{V}, I_D=-1\text{A}$	--	65	94	$\text{m}\Omega$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated) (Note 3)

Ciss	Input Capacitance	$V_{DS}=-10\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	--	531	--	pF
Coss	OutputCapacitance		--	72	--	pF
Crss	ReverseTransferCapacitance		--	67	--	pF
Qg	Total Gate Charge	$V_{DS}=-10\text{V}, I_D=-3\text{A}, V_{GS}=-4.5\text{V}$	--	8.3	--	nC
Qgs	Gate-SourceCharge		--	1.2	--	nC
Qgd	Gate-DrainCharge		--	1.6	--	nC

Switching Characteristics (Note 3)

Td(on)	Turn-on Delay Time	$V_{DS}=-10\text{V}, I_D=-1\text{A}, R_G=10\Omega, V_{GS}=-4.5\text{V}$	--	12	--	ns
Tr	Turn-on Rise Time		--	35	--	ns
Td(off)	Turn-Off Delay Time		--	30	--	ns
Tf	Turn-Off Fall Time		--	10	--	ns

Source- Drain Diode Characteristics@ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

ISD	Source-Drain Current (Body Diode)	--	--	-3	A	
ISM	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-12	A	
VSD	Forward on voltage	$I_S = -3.0\text{A}, V_{GS}=0\text{V}$	--	--	-1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Device mounted on FR-4 PCB, 1inch x 0.85inch x 0.062 inch
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

P- Channel Typical Characteristics

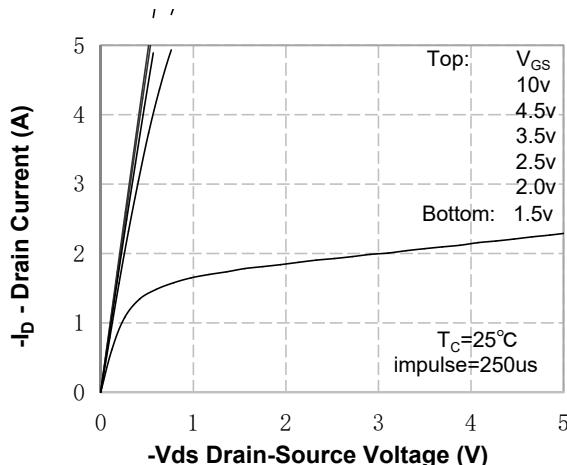


Figure 1. On-Region Characteristics

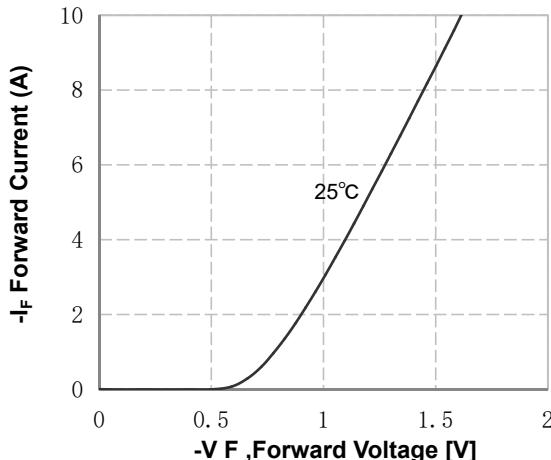


Figure 4. Body Diode Forward Voltage Variation with Source Current

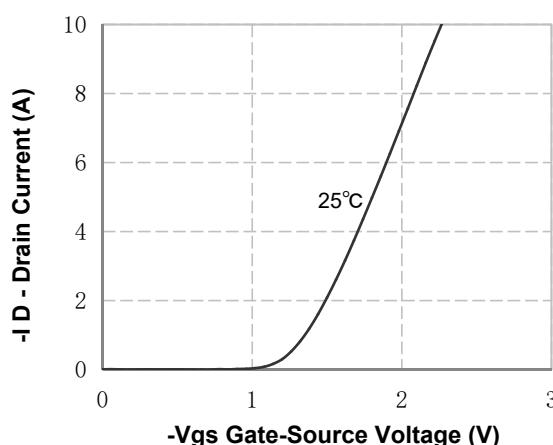


Figure 2: Transfer Characteristics

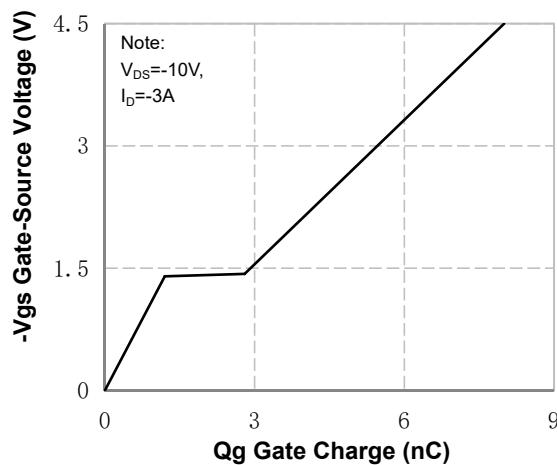


Figure 5. Gate Charge Characteristics

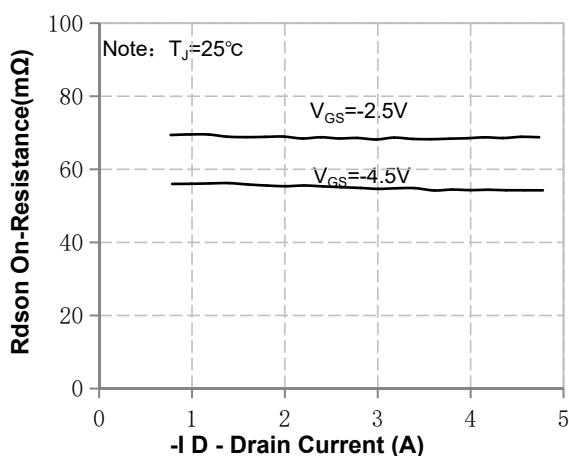


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

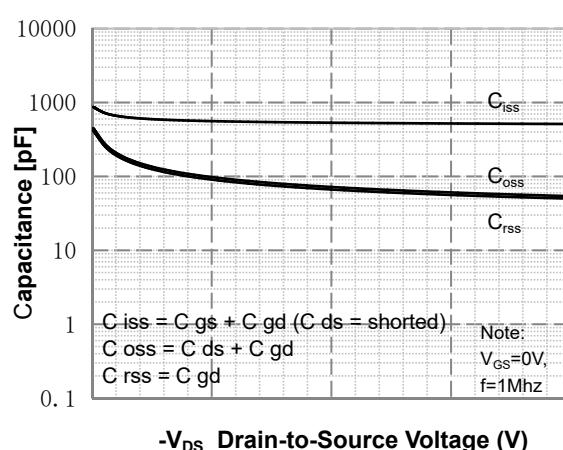


Figure 6. Capacitance Characteristics

P- Channel Typical Characteristics (Continued)

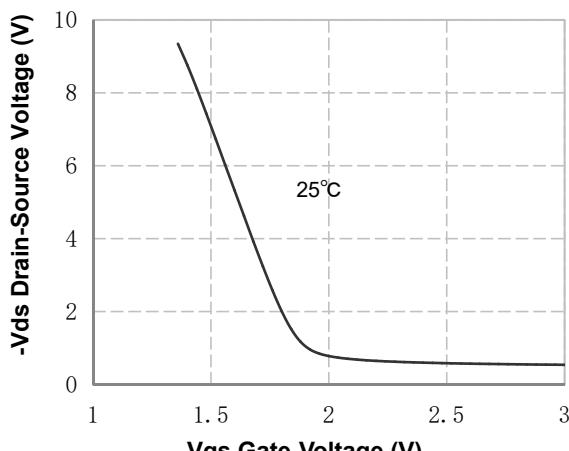


Figure 7. V_{ds} Drain-Source Voltage vs Gate Voltage

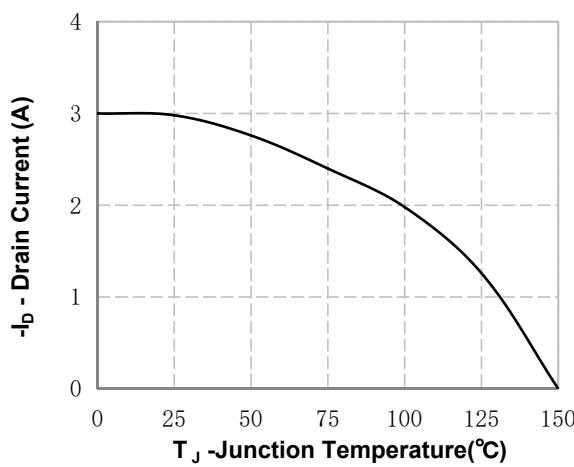


Figure 9. Maximum Continuous Drain Current vs Temperature

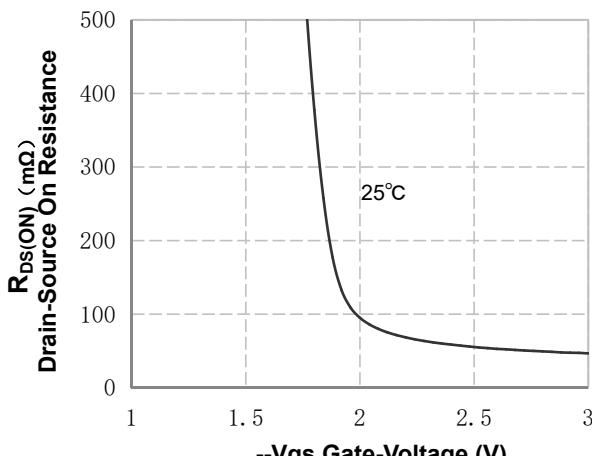


Figure 8. On-Resistance vs Gate Voltage

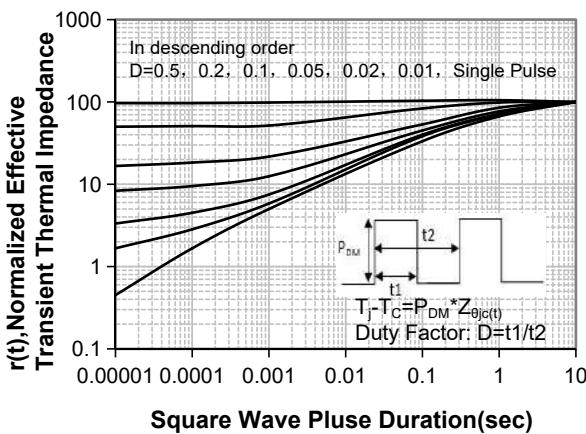


Figure 10. Transient Thermal Response Curve

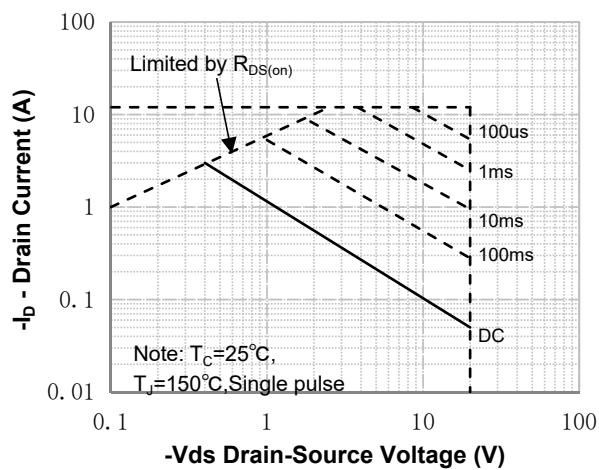
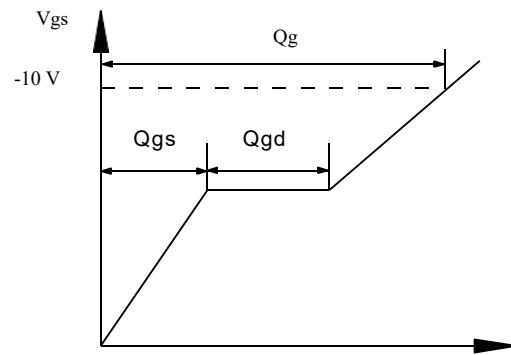
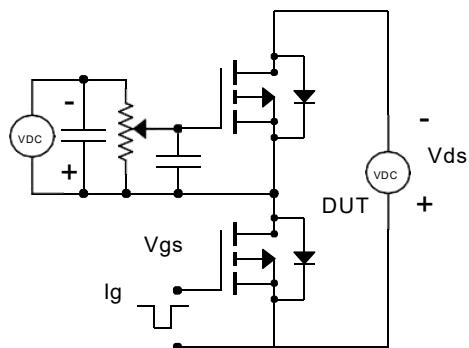


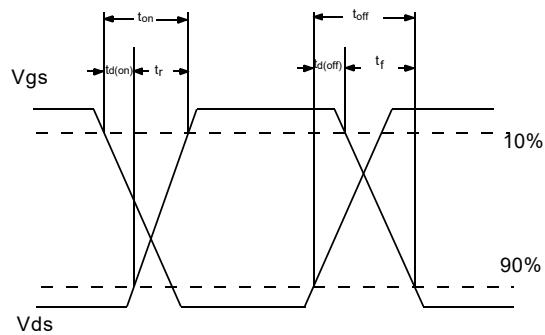
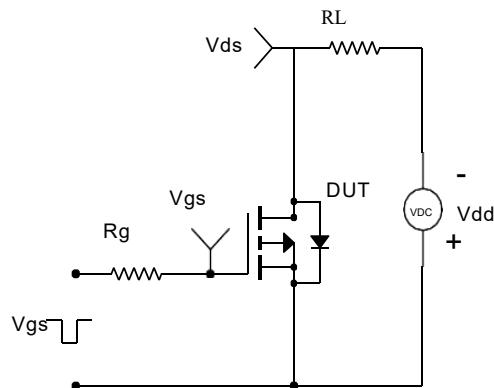
Figure 11. Maximum Safe Operating Area



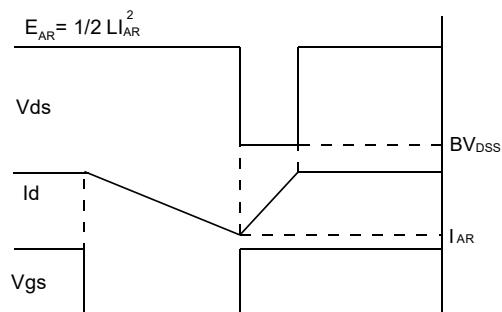
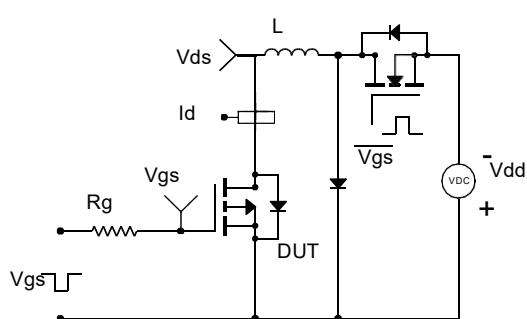
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

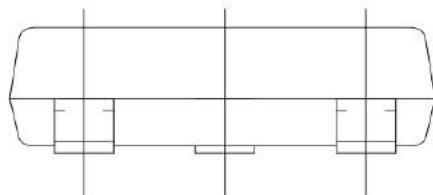
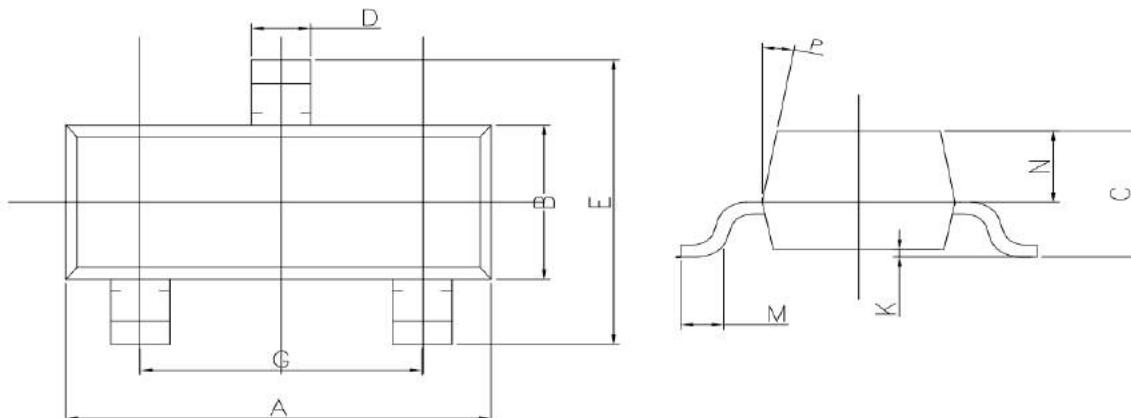


Unclamped Inductive Switching Test Circuit & Waveforms





SOT-23 Package Information



DIM	MILLIMETERS
A	2.90 ± 0.1
B	1.30 ± 0.10
C	0.90 ~ 1.15
D	0.40 ± 0.1
E	2.40 ± 0.15
G	1.90 ± 0.10
K	0.00~0.10
M	0.30MIN
N	0.60 ± 0.10
P	10°TYP

Customer Service

Sales and Service:

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